

TSMC-01-380



February 22, 2002

To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572  
20 McIntosh Drive  
Poughkeepsie, N.Y. 12603

1765  
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MAR 14 2002  
TC 1700

Subject: | Serial No. 10/036,898 01/04/02 |  
| Shao Yen Ku |  
| A SUCCESSFUL AND EASY METHOD TO |  
| REMOVE POLYSILICON FILM |  
Grp. Art Unit: 1765

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56. Copies of each document is included herewith.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner of Patents and  
Trademarks, Washington, D.C. 20231, on February 27, 2002.

Stephen B. Ackerman, Reg.# 37761

Signature/Date Stephen B. Ackerman 2/27/02

U.S. Patent 5,928,969 to Li et al., "Method for Controlled Selective Polysilicon Etching," describes a method for controlled selective polysilicon etching employing an  $\text{NH}_4\text{OH}$  plus  $\text{NH}_4\text{F}$  polysilicon etch and a hemispherical grain (HSG) polysilicon process.

U.S. Patent 6,100,203 to Kil et al., "Methods of Employing Aqueous Cleaning Compositions in Manufacturing Microelectronic Device," describes a polysilicon etch and subsequent aqueous cleaning composition cleaner methods.

U.S. Patent 5,431,777 to Austin et al., "Methods and Compositions for the Selective Etching of Silicon," describes methods and compositions for the selective etching of silicon.

U.S. Patent 5,296,093 to Szwejkowski et al., "Process for Removal of Residues Remaining After Etching Polysilicon Layer in Formation of Integrated Circuit Structure," describes a process for removal of residues remaining after etching a polysilicon layer.

U.S. Patent 5,030,590 to Amini et al., "Process for Etching Polysilicon Layer in Formation of Integrated Circuit Structure," describes a process for etching a polysilicon layer in the formation of an integrated circuit structure.

U.S. Patent 4,113,551 to Bassous et al., "Polycrystalline Silicon Etching with Tetramethylammonium Hydroxide," describes a method for polycrystalline silicon etching with tetramethylammonium hydroxide.

U.S. Patent 5,963,804 to Figura et al., "Method of Making a Doped Silicon Structure with Impression Image on Opposing Roughened Surfaces," describes a method of making a doped silicon structure with an impression image on opposing roughened surfaces.

U.S. Patent 5,976,767 to Li, "Ammonium Hydroxide Etch of Photoresist Masked Silicon," describes a process for selectively removing silicon containing material using an ammonium hydroxide etch.

Sincerely,

*Stephen B. Ackerman*  
Stephen B. Ackerman,  
Reg. No. 37761

INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION

MAR 07 2002

(Use several sheets if necessary)

Docket Number (Optional)

TSMC-01-580

Application Number

10/036, 898

Applicant

Shao Yen Ku

Filing Date

01/04/02

Group Art Unit

1765

## U. S. PATENT DOCUMENTS

EXAMINER'S INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	ALSO DATE IF APPROPRIATE
BT	5928969	7/27/99	Li et al.	438	753	1/22/96
BT	6100203	8/8/00	Kil et al.	438	745	7/16/98
BT	5431777	7/11/95	Austin et al.	156	622.1	9/17/92
BT	5296093	3/22/94	Szwejkowski et al.	156	643	5/27/92
BT	5030590	7/9/91	Amini et al.	437	233	6/9/89
BT	4113551	9/12/78	Bassous et al.	156	662	12/16/77
BT	5963804	10/5/99	Figura et al.	438	255	3/14/97
BT	5976767	11/2/99	Li	430	313	10/9/97

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)


EXAMINER

Binh Truan

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5/2/05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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